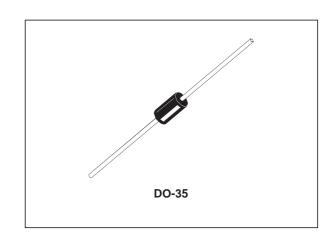


SMALL SIGNAL SCHOTTKY DIODE



DESCRIPTION

General purpose, metalto silicon diode featuring high breakdown voltage low turn-on voltage.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	100	V
I _F	Forward Continuous Current*	150	mA
I _{FRM}	Repetitive Peak Forward Current*	350	mA
I _{FSM}	Surge non Repetitive Forward Current*	750	mA
P _{tot}	Power Dissipation*	150	mW
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C
TL	Maximum Temperature for Soldering during Case	230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	300	°C/W

^{*} On infinite heatsink with 4mm lead length.

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Тур.	Max.	Unit
V _{BR}	T _j = 25°C	$I_R = 100 \mu A$	100			V
V _F *	T _j = 25°C	$I_F = 0.1 \text{mA}$			0.25	V
	$T_j = 25^{\circ}C$	I _F = 10mA			0.45	
	$T_j = 25^{\circ}C$	I _F = 250mA			1	
I _R *	T _j = 25°C	V _R = 1.5V			0.5	μΑ
	$T_j = 60$ °C				5	
	T _j = 25°C	V _R = 10V			0.8	
	$T_j = 60$ °C				7.5	
	T _j = 25°C	V _R = 50V			2	
	$T_j = 60$ °C				15	
	T _j = 25°C	V _R = 75V			5	
	$T_j = 60$ °C				20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
	T _j = 25°C	$V_R = 0V$	f = 1Mhz		10		pF
	T _j = 25°C	$V_R = 1V$	1 - 11/11/2		6		

^{*} Pulse test: $t_p \le 300 \mu s \ \delta < 2\%$.

Fig. 1-1: Forward voltage drop versus forward current (low level, typical values)

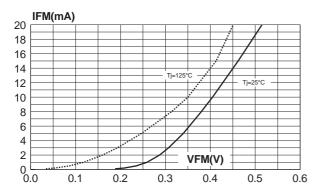


Fig. 1-2: Forward voltage drop versus forward current (high level, typical values)

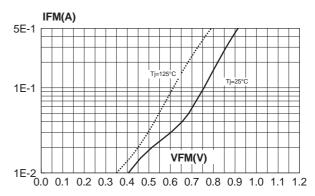


Fig. 2: Leakage current versus reverse voltage applied (typical values)

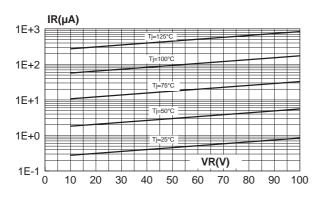


Fig. 3: Leakage current versus junction temperature (typical values)

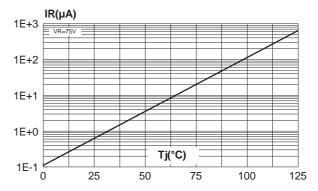
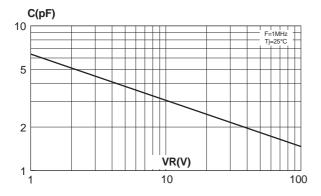


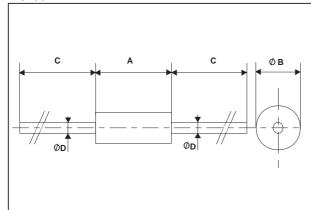
Fig. 4: Junction capacitance versus reverse voltage applied (typical values)



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PACKAGE MECHANICAL DATA

DO-35



REF.	DIMENSIONS				
	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
А	3.05	4.50	0.120	0.177	
В	1.53	2.00	0.060	0.079	
С	28.00		1.102		
D	0.458	0.558	0.018	0.022	

Cooling method: by convection and conduction

Marking: clear, ring at cathode end

• Weight: 0.15g

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